Please replace claim 24 with the following amended claim.

24. (Twice amended) A non-crystalline oxide represented by the formula (II):

$$(Al_2O_3)_j(M_nO_m)_k \qquad (II)$$

wherein:

Al is aluminum;

O is oxygen;

M is selected from the group consisting of scandium (Sc), lanthanum (La), actinium (Ac), titanium (Ti), zirconium (Zr), hafnium (Hf), and rutherfordium (Rf); and

j ranges from about 0.5 to about 4.5; k is equal to about 1; n ranges from about 0.5 to about 2.5, and m ranges from about 1.5 to about 3.5.

Please replace claim 25 with the following amended claim.

25. (Amended) The oxide according to Claim 24, wherein M is hafnium (Hf) or zirconium (Zr), n is 1, m is 2, j is 4, and k is 1.

Please replace claim 26 with the following amended claim.

26. (Amended) The oxide according to Claim 24, wherein M is lanthanum (La), n is 2, m is 3, j is 3, and k is 1.

Please replace claim 34 with the following amended claim.

34. (Twice amended) A field effect transistor comprising:

an integrated circuit substrate having a first surface;

source and drain regions in said substrate at said first surface in a spaced apart relationship; and

a gate insulating layer on said substrate at said first surface between said spaced apart source and drain regions, said gate insulating layer comprising a non-crystalline oxide represented by the formula (II):

$$(Al_2O_3)_j(M_nO_m)_k \qquad (II)$$

wherein:

Al is aluminum, O is oxygen, M is selected from the group consisting of scandium (Sc), lanthanum (La), actinium (Ac), titanium (Ti), zirconium (Zr), hafnium (Hf), and rutherfordium (Rf), j ranges from about 0.5 to about 4.5, k is equal to about 1, n ranges from about 0.5 to about 2.5, and m ranges from about 1.5 to about 3.5.

Please replace claim 37 with the following amended claim.

37. (Amended) The field effect transistor according to Claim 34, wherein M is hafnium (Hf) or zirconium (Zr), n is 1, m is 2, j is 4, and k is 1.

Please replace claim 38 with the following amended claim.

38. (Amended) The field effect transistor according to Claim 34, wherein M is lanthanum (La), n is 2, m is 3, j is 3, and k is 1.

Please add the following new claim.

47. (New) A non-crystalline oxide represented by the formula $(Al_2O_3)_3(La_2O_3)$ (III).

48. (New) A field effect transistor comprising:

an integrated circuit substrate having a first surface;

source and drain regions in said substrate at said first surface in a spaced apart relationship; and

a gate insulating layer on said substrate at said first surface between said spaced apart source and drain regions, said gate insulating layer comprising a non-crystalline oxide represented by the formula (III):

$$(Al_2O_3)_3(La_2O_3).$$